

Docket No.: 49657-904

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Yoshinori TANAKA, et al.

Serial No.:

(Divisional of Serial No. 09/095,612)

Group Art Unit:

Filed: January 10, 2001

Examiner:

For: SEMICONDUCTOR DEVICE COMPRISING CAPACITOR AND METHOD OF
FABRICATING THE SAME

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

Prior to examination of the above-referenced application, please amend the application as follows:

IN THE CLAIMS:

Please add new claims 21 through 24 as follows:

--21. The semiconductor device in accordance with claim 12, wherein
said part of said insulating film having a width being smaller than the minimum working
size formable by photolithography.

22. The semiconductor device in accordance with claim 21, wherein
a side surface of said capacitor lower electrode has a curved plane.

23. The semiconductor device in accordance with claim 21, wherein
said insulating film includes an upper insulating film and a lower insulating film being

different in etching rate from each other.

24. The semiconductor device in accordance with claim 21, comprising:

said capacitor upper electrode being formed to extend toward said peripheral circuit region,

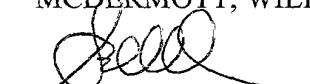
an upper interlayer isolation film being formed on said capacitor upper electrode and having a contact hole exposing a surface of said capacitor upper electrode, and a peripheral circuit element protection film being formed under said insulating film in a region located under said contact hole.--

REMARKS

Entry of this preliminary amendment is respectfully requested.

Respectfully submitted,

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